

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25 ℃
-70V	160mΩ @ V _{GS} = -10V	-2.6A
-70V	$250m\Omega @ V_{GS}= -4.5V$	-1.6A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- **DC-DC Converters**
- **Power Management Functions**
- Uninterrupted Power Supply



70V P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production •
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

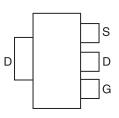
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.112 grams (Approximate)

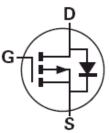


SOT223

Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

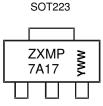
	Part Number	Qualification	Case	Packaging		
ZXMP7A17GTA Co		Commercial	SOT223	1,000/Tape & Reel		
Notes:	Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.					

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP7A17 = Product Type Marking Code YWW_= Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or WW = Week Code $(01 \sim 53)$



Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	-70	V	
Gate-Source Voltage			V _{GS}	±20	V	
		(Note 6)		-3.7		
Continuous Drain Current	$V_{GS} = -10V$	T _A = +70 °C (Note 6)	ID	-2.9	А	
		(Note 5)		-2.6		
Pulsed Drain Current	V _{GS} = -10V	(Note 7)	I _{DM}	-9.6	A	
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	Is	-4.8	А	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	-9.6	A		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	2.0 16.0	W	
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/℃	
Thermal Resistance, Junction to Ambient	(Note 5) (Note 6)	R _{θJA}	62.5 34	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-70	_	_	V	I _D = -250µA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -70V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
ON CHARACTERISTICS			•	•	•		
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	_	V	I _D = -250µA, V _{DS} = V _{GS}	
Static Drain-Source On-Resistance (Note 8)	D			0.16 0.25 Ω	V _{GS} = -10V, I _D = -2.1A		
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}		_		<u> </u>	V _{GS} = -4.5V, I _D = -1.7A	
Forward Transconductance (Notes 8 & 9)	g _{fs}	_	4.4	_	S	V _{DS} = -15V, I _D = -2.1A	
Diode Forward Voltage (Note 8)	V _{SD}	_	-0.85	-0.95	V	I _S = -2.0A, V _{GS} = 0V	
Reverse recovery time (Note 9)	t _{rr}		29.8	_	ns	-I _S = -2.1A, di/dt= 100A/μs	
Reverse recovery charge (Note 9)	Q _{rr}		38.5	—	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		635	—	pF	V _{DS} = -40V, V _{GS} = 0V - f= 1MHz	
Output Capacitance	Coss		52	—	pF		
Reverse Transfer Capacitance	C _{rss}		42.5	_	pF		
Total Gate Charge (Note 10)	Qg		9.6	_	nC	V _{GS} = -5V	
Total Gate Charge (Note 10)	Qg	_	18	_	nC		V _{DS} = -35V
Gate-Source Charge (Note 10)	Q _{gs}	_	1.77	_	nC	V _{GS} = -10V	I _D = -2.1A
Gate-Drain Charge (Note 10)	Q _{gd}	_	3.66	_	nC	1	
Turn-On Delay Time (Note 10)	t _{D(on)}		2.5	_	ns	V _{DD} = -35V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω	
Turn-On Rise Time (Note 10)	tr		3.4	_	ns		
Turn-Off Delay Time (Note 10)	t _{D(off)}		27.9	_	ns		
Turn-Off Fall Time (Note 10)	t _f	_	8	_	ns		

Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as Note 5, except the device is measured at $t \le 5$ seconds.

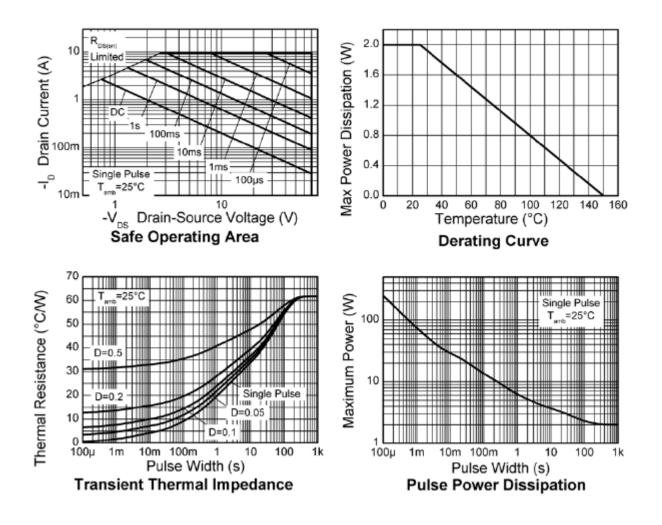
7. Same as Note 5, except the device is pulsed with D= 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.

8. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.

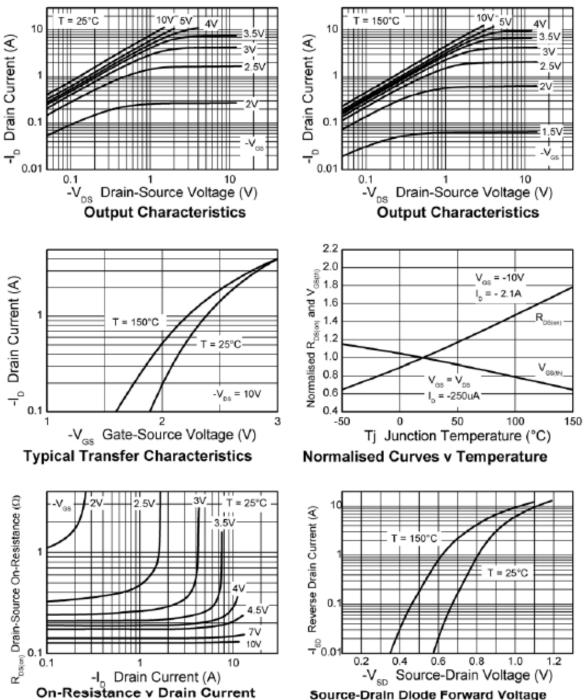
9. For design aid only, not subject to production testing.

10. Switching characteristics are independent of operating junction temperatures.



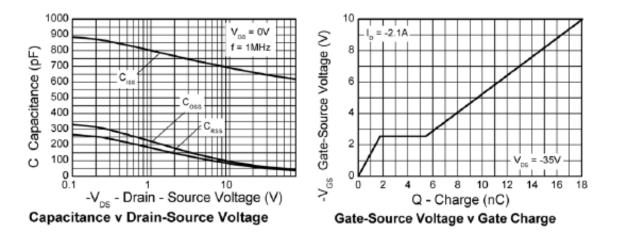






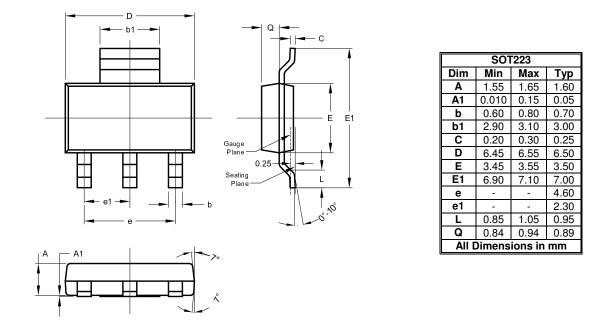
Source-Drain Diode Forward Voltage





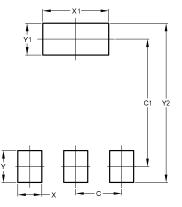
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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